

FIG. 2 (PRIOR ART)

TITLE: STRAINED SEMICONDUCTOR BY FULL WAFER BONDING INVENTORS NAME: Leonard Forbes et al.

DOCKET NO.: 1303.109US1

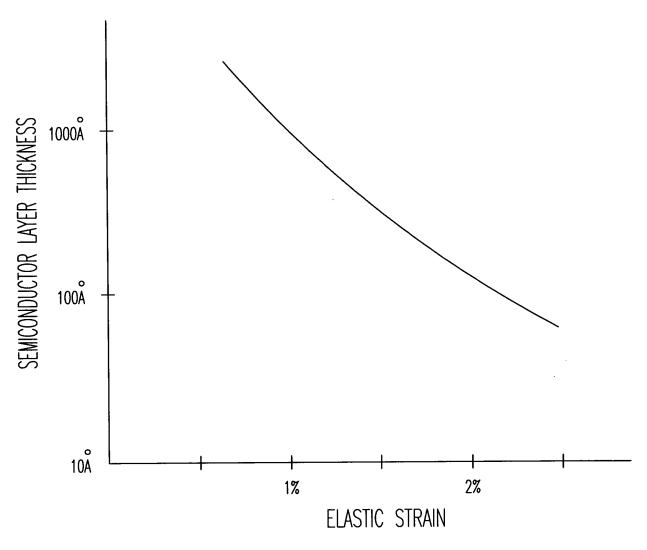


FIG. 3 (PRIOR ART)

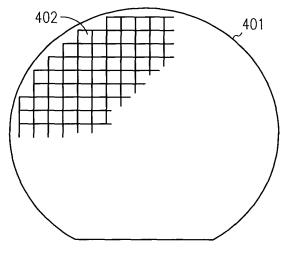


FIG. 4A

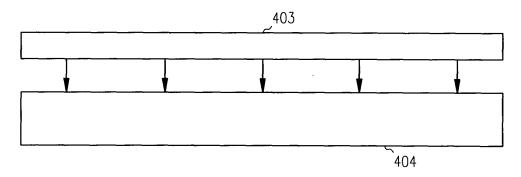


FIG. 4B

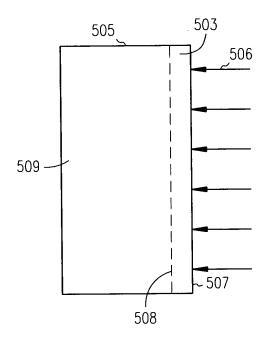
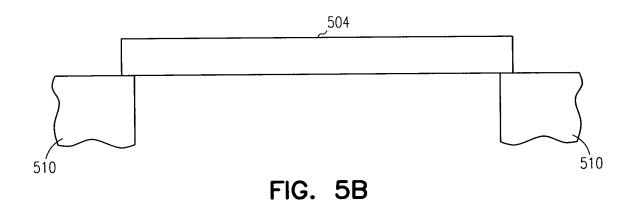
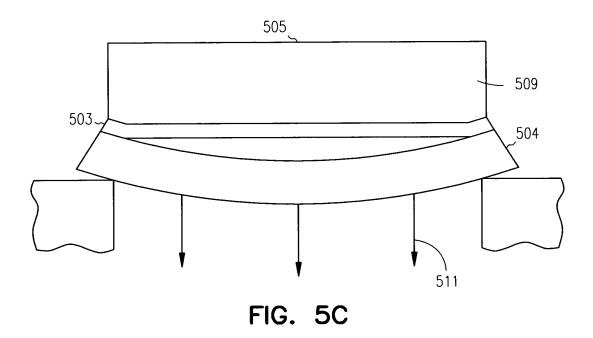


FIG. 5A



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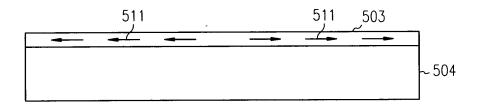
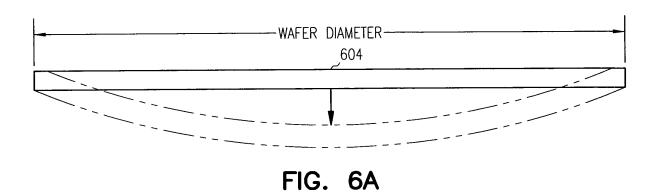


FIG. 5D

TITLE: STRAINED SEMICONDUCTOR BY FULL WAFER BONDING

INVENTORS NAME: Leonard Forbes et al. DOCKET NO.: 1303.109US1



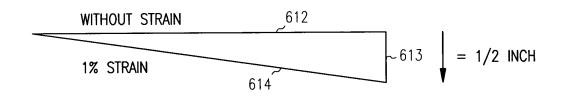


FIG. 6B

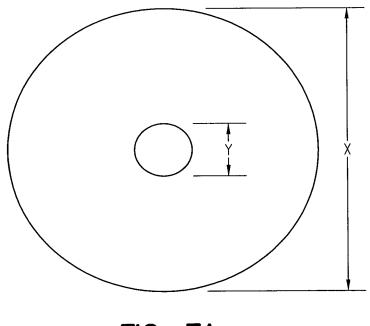


FIG. 7A

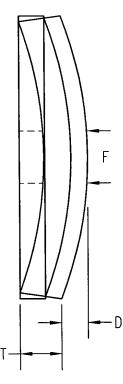


FIG. 7B

TITLE: STRAINED SEMICONDUCTOR BY FULL WAFER BONDING

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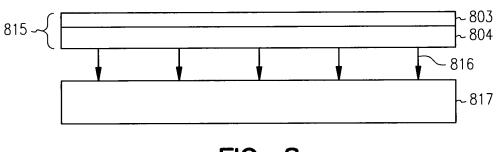
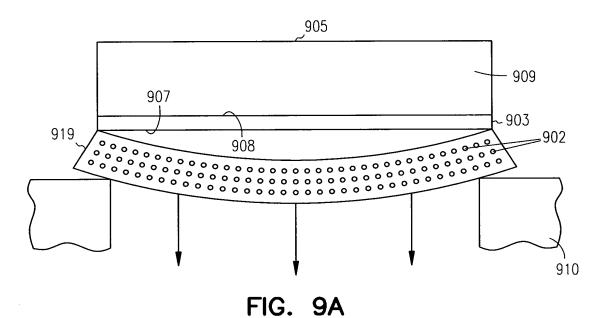


FIG. 8



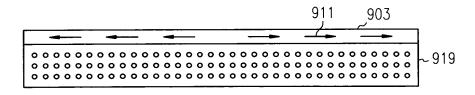
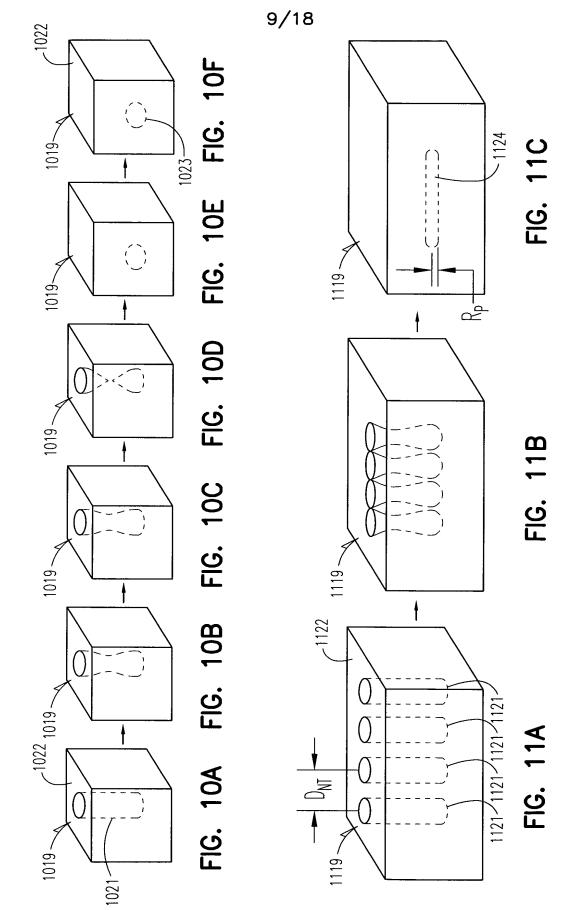
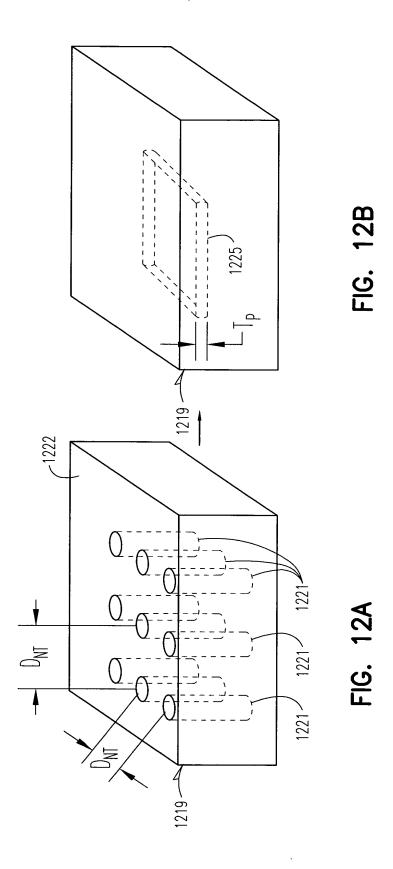
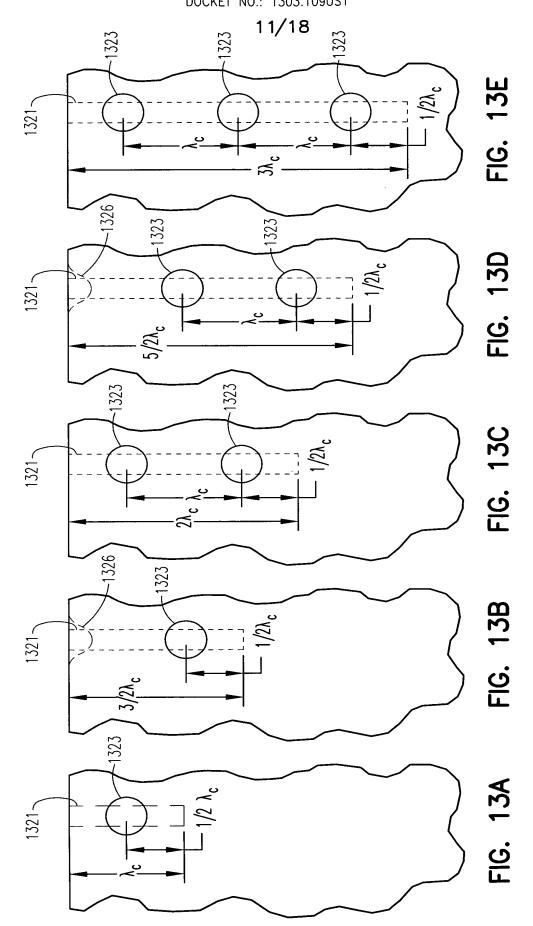


FIG. 9B







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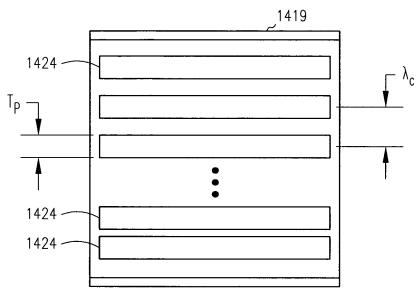
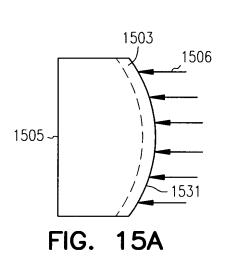
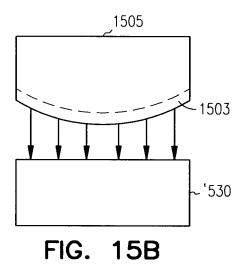


FIG. 14





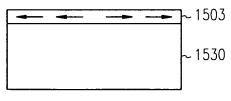


FIG. 15C

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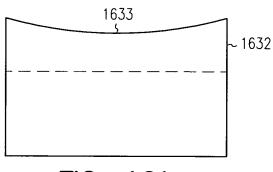


FIG. 16A

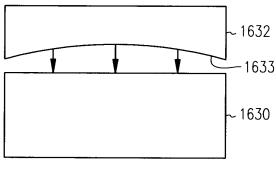


FIG. 16B

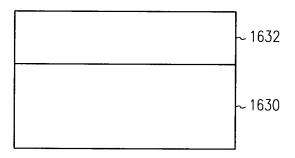


FIG. 16C

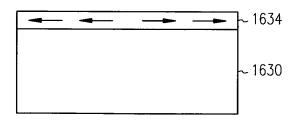


FIG. 16D

INVENTORS NAME: Leonard Forbes et al. DOCKET NO.: 1303.109US1 14/18 1740 FORM A PREDETERMINED BOWED CONTOUR IN A FLEXIBLE ONE OF A WAFER-SIZED SEMICONDUCTOR MEMBRANE AND A SUBSTRATE WAFER 1741 BOND THE WAFER-SIZED SEMICONDUCTOR MEMBRANE TO THE SUBSTRATE WAFER / STRAIGHTEN THE PREDETERMINED BOWED CONTOUR FIG. 17 1840۔ APPLY FORCE TO BOW FLEXIBLE SUBSTRATE WAFER 1842 BOND PERIPHERY OF WAFER-SIZED SEMICONDUCTOR MEMBRANE TO PERIPHERY OF THE SUBSTRATE WAFER ~ 1841 REMOVE FORCE ALLOWING THE FLEXIBLE SUBSTRATE WAFER TO STRAIGHTEN FIG. 18 1940 APPLY FORCE TO BOW THIN SUBSTRATE 1942 BOND PERIPHERY OF WAFER-SIZED SEMICONDUCTOR MEMBRANE TO PERIPHERY OF THE SUBSTRATE WAFER 1943 ~ 1941 REMOVE FORCE ALLOWING THE FLEXIBLE SUBSTRATE WAFER TO STRAIGHTEN 1944 BOND COMPOSITE OF MEMBRANE AND THIN SUBSTRATE TO THICKER CARRIER SUBSTRATE

TITLE: STRAINED SEMICONDUCTOR BY FULL WAFER BONDING

FIG. 19

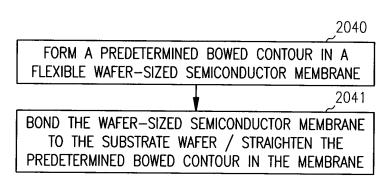


FIG. 20

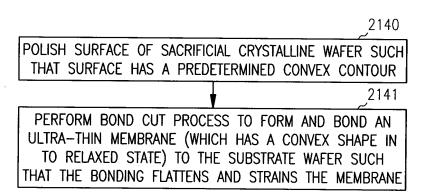


FIG. 21

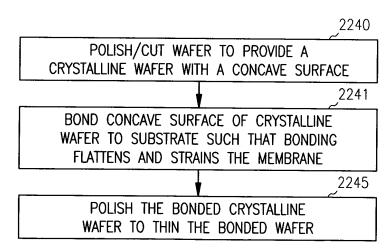


FIG. 22

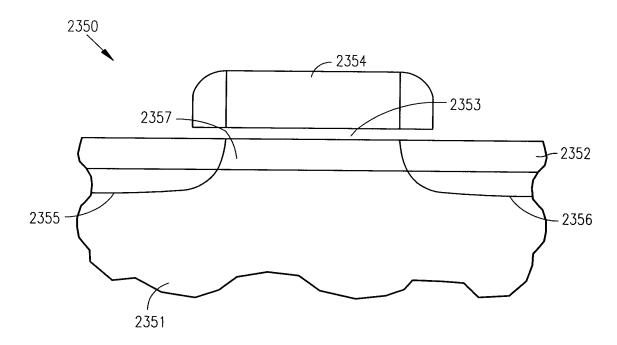
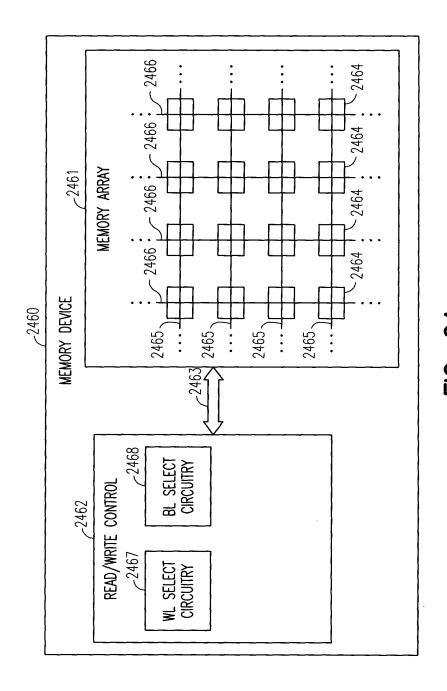


FIG. 23

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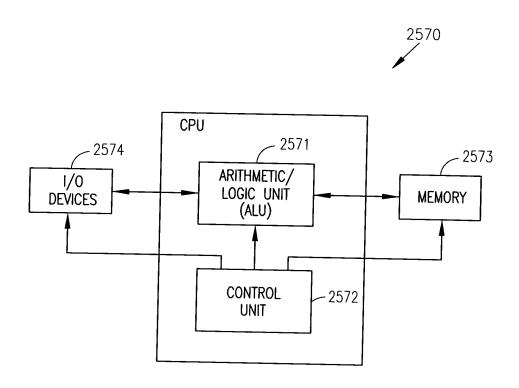


FIG. 25